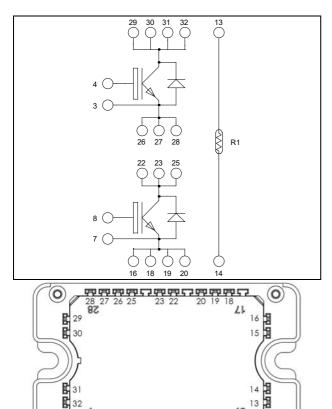


Power Matters."

Phase leg Trench + Field Stop IGBT3 Power Module



Pins 29/30/31/32 must be shorted together Pins 26/27/28/22/23/25 must be shorted together to achieve a phase leg Pins 16/18/19/20 must be shorted together

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APTGT200A60T3AG

$V_{CES} = 600V$

$I_C = 200A$ @ $T_c = 100^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

0

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	290	
I _C	Continuous Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	200	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Power Dissipation	$T_C = 25^{\circ}C$	750	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	400A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Power Matters."

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
V _{CE(sat)}		$I_C = 200A$	$T_j = 150^{\circ}C$		1.7		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			12.3		
Coes	Output Capacitance	$V_{CE} = 25V$			0.8		nF
Cres	Reverse Transfer Capacitance	f = 1 MHz			0.4		
Q_{G}	Gate charge	$V_{GE} = \pm 15V$; $V_{CE} = 300V$ $I_{C} = 200A$			2.2		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			115		
Tr	Rise Time	$V_{GE} = \pm 15V$			45		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 200A$			225		
T_{f}	Fall Time	$R_G = 2\Omega$		55			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 2\Omega$			130		
Tr	Rise Time				50		ns
T _{d(off)}	Turn-off Delay Time				300		
T _f	Fall Time				70		
Б	Turn on Engineer	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		1		
Eon	Turn on Energy	$V_{Bus} = 300V$	$T_j = 150^{\circ}C$		1.8		mJ
Б		$I_{\rm C} = 200 {\rm A}$	$T_j = 25^{\circ}C$		5.7		т
E_{off}	Turn off Energy	$R_G = 2\Omega \qquad \qquad T_j = 150^{\circ}C$			7		mJ
Isc	Short Circuit data	$\begin{array}{l} V_{GE} \!\leq\! \! 15V \; ; \; V_{Bus} \!=\! 360V \\ t_p \!\leq\! 6\mu s \; ; \; T_j \!=\! 150^{\circ}C \end{array}$			1000		А
R_{thJC}	Junction to Case Thermal Resistance					0.20	°C/W

Reverse diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					600	V
I _{RM}	Reverse Leakage Current	$V_{R} = 600V$				250	μΑ
I_F	DC Forward Current		$Tc = 80^{\circ}C$		200		Α
V	Diode Forward Voltage	$I_F = 200A$	$T_j = 25^{\circ}C$		1.6	2	V
V_{F}		$V_{GE} = 0V$	$T_j = 150^{\circ}C$		1.5		v
	D T'		$T_j = 25^{\circ}C$		125		
t_{rr}	Reverse Recovery Time		$T_j = 150^{\circ}C$		220		ns
0	Paulana Pasayany Changa	$I_{\rm F} = 200 {\rm A}$	$T_j = 25^{\circ}C$		9		
Qn	Reverse Recovery Charge	$V_{\rm R} = 300 V$ di/dt = 2800 A/µs	$T_j = 150^{\circ}C$		20		μC
En	Parama Pasariamy En anov		$T_j = 25^{\circ}C$		2.2		
Er	Reverse Recovery Energy		$T_j = 150^{\circ}C$		4.8		mJ
R_{thJC}	Junction to Case Thermal Resistance					0.31	°C/W



Power Matters."

Thermal and package characteristics

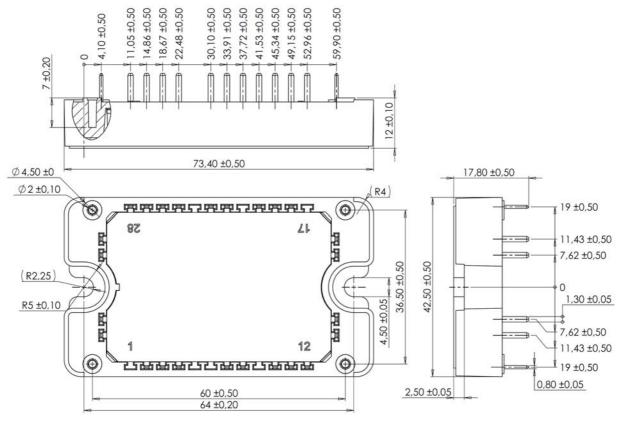
Symbol	Characteristic			Min	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
TJ	Operating junction temperature range			-40	175	
T _{JOP}	Recommended junction temperature under switching conditions		-40	T _J max -25	°C	
T _{STG}	Storage Temperature Range		-40	125	C	
T _C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		Κ
$\Delta B/B$		$T_C = 100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

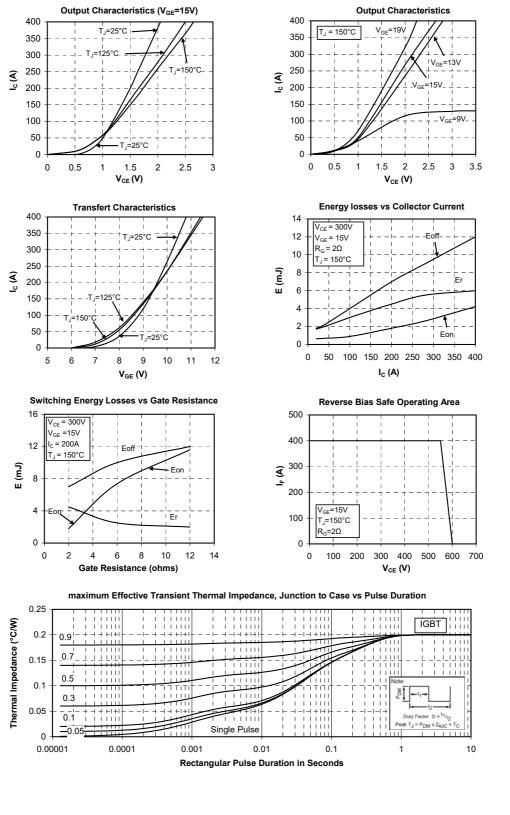
www.microsemi.com

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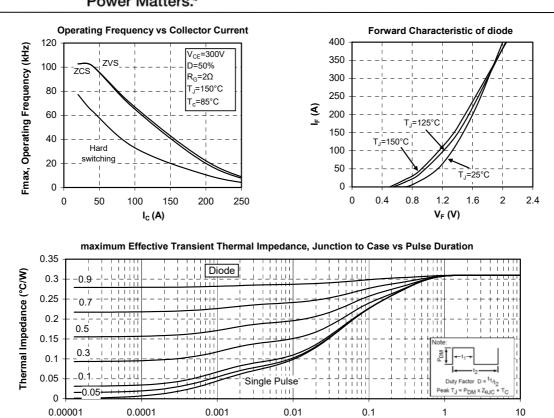
Power Matters."

Typical Performance Curve



APTGT200A60T3AG





Rectangular Pulse Duration in Seconds



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